NL17SG14

Schmitt Inverter

The NL17SG14 MiniGate™ is an advanced high−speed CMOS Schmitt Inverter in ultra−small footprint.

The NL17SG14 input structure provides protection when voltages up to 4.6 V are applied.

Features

- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: t_{PD} = 3.7 ns (Typ) at V_{CC} = 3.0 V, C_L = 15 pF
- Low Power Dissipation: I_{CC} = 0.5 μA (Max) at T_A = 25°C
- 4.6 V Overvoltage Tolerant (OVT) Input Pins
- Ultra−Small Packages
- These are Pb−Free and Halide−Free Devices

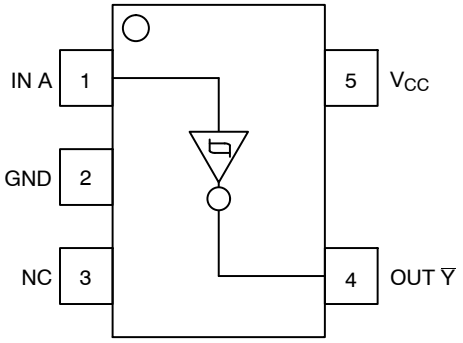

Figure 1. Pinout

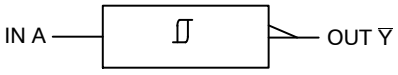

Figure 2. Logic Symbol

ON Semiconductor®

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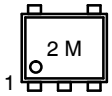
MARKING DIAGRAM

SOT−953
CASE 527AE



2 = Specific Device Code
M = Month Code

PIN ASSIGNMENT	
1	IN A
2	GND
3	NC
4	OUT Y
5	V_{CC}

FUNCTION TABLE

A Input	Y Output
L	H
H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +5.5	V
V_{IN}	DC Input Voltage		−0.5 to +4.6	V
V_{OUT}	DC Output Voltage	Output at High or Low State Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +4.6	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−20	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND	−20	mA
I_{OUT}	DC Output Source/Sink Current		±20	mA
I_{CC}	DC Supply Current per Supply Pin		±20	mA
I_{GND}	DC Ground Current per Ground Pin		±20	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >100	V
$I_{LATCHUP}$	Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 4)	±100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2−ounce copper trace with no air flow.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		0.9	3.6	V
V_{IN}	Digital Input Voltage		0.0	3.6	V
V_{OUT}	Output Voltage	Output at High or Low State Power−Down Mode (V_{CC} = 0 V)	0.0 0.0	V_{CC} 3.6	V
T_A	Operating Temperature Range		−55	+125	°C
$\Delta t / \Delta V$	Input Transition Rise or Fail Rate	V_{CC} = 3.3 V ± 0.3 V	0	10	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition		V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Unit
					Min	Typ	Max	Min	Max	
V_{T+}	Positive−Going Input Threshold Voltage			0.9		0.7	0.86		0.87	V
				1.1		0.81	0.95		1	
				1.4		0.94	1.16		1.2	
				1.65		1.06	1.25		1.3	
				2.3		1.36	1.6		1.65	
				3.0		1.8	2.05		2.1	
V_{T-}	Negative−Going Input Threshold Voltage			0.9	0.09	0.23		0.08		V
				1.1	0.15	0.33		0.12		
				1.4	0.3	0.47		0.25		
				1.65	0.35	0.6		0.3		
				2.3	0.55	0.85		0.5		
				3.0	0.95	1.13		0.9		
V_H	Hysteresis Voltage			0.9	0.15	0.5	0.75	0.2	0.8	V
				1.1	0.15	0.5	0.75	0.2	0.8	
				1.4	0.15	0.5	0.75	0.2	0.8	
				1.65	0.15	0.5	0.75	0.2	0.8	
				2.3	0.15	0.5	0.75	0.2	0.8	
				3.0	0.25	0.65	0.85	0.3	0.9	
V_{OH}	High−Level Output Voltage	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −20 μA	0.9	0.75			0.75		V
			I_{OH} = −0.3 mA	1.1 to 1.3	0.75 x V_{CC}			0.75 x V_{CC}		
			I_{OH} = −1.7 mA	1.4 to 1.6	0.75 x V_{CC}			0.75 x V_{CC}		
			I_{OH} = −3.0 mA	1.65 to 1.95	V_{CC} − 0.45			V_{CC} − 0.45		
			I_{OH} = −4.0 mA	2.3 to 2.7	2.0			2.0		
			I_{OH} = −8.0 mA	3.0 to 3.6	2.48			2.48		
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 20 μA	0.9			0.1		0.1	V
			I_{OL} = 0.3 mA	1.1 to 1.3			0.25 x V_{CC}		0.25 x V_{CC}	
			I_{OL} = 1.7 mA	1.4 to 1.6			0.25xV cc		0.25 x V_{CC}	
			I_{OL} = 3.0 mA	1.65 to 1.95			0.45		0.45	
			I_{OL} = 4.0 mA	2.3 to 2.7			0.4		0.4	
			I_{OL} = 8.0 mA	3.0 to 3.6			0.4		0.4	
I_{IN}	Input Leakage Current	0 ≤ V_{IN} ≤ 3.6 V		0 to 3.6			±0.1		±1.0	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND		3.6			0.5		10.0	μA

AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f = 3.0$ ns

Symbol	Parameter	Test Condition	V_{CC} (V)	T_A = 25 °C			T_A = −55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, A or $\overline{Y}$	C_L = 10 pF, R_L = 1 MΩ	0.9	–	27.3	–	–	–	ns
			1.1 to 1.3	–	13.0	22.6	1.0	35.9	
			1.4 to 1.6	–	7.5	10.5	1.0	11.3	
			1.65 to 1.95	–	6.0	7.8	1.0	8.2	
			2.3 to 2.7	–	4.3	5.4	1.0	5.8	
			3.0 to 3.6	–	3.5	4.4	1.0	4.6	
		C_L = 15 pF, R_L = 1 MΩ	0.9	–	29.5	–	–	–	ns
			1.1 to 1.3	–	14.3	25.1	1.0	41.6	
			1.4 to 1.6	–	8.0	11.5	1.0	12.6	
			1.65 to 1.95	–	6.3	8.4	1.0	8.7	
			2.3 to 2.7	–	4.6	5.7	1.0	6.1	
			3.0 to 3.6	–	3.7	4.6	1.0	5.0	
		C_L = 30 pF, R_L = 1 MΩ	0.9	–	40.5	–	–	–	ns
			1.1 to 1.3	–	19.6	35.7	1.0	58.1	
			1.4 to 1.6	–	10.7	15.8	1.0	17.6	
			1.65 to 1.95	–	7.8	10.7	1.0	11.7	
			2.3 to 2.7	–	5.4	6.9	1.0	8.1	
			3.0 to 3.6	–	4.3	5.2	1.0	6.1	
C_{IN}	Input Capacitance		0 to 3.6		3	–	–	–	pF
C_O	Output Capacitance	V_O = GND	0		3	–	–	–	pF
C_{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	–	4	–	–	–	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

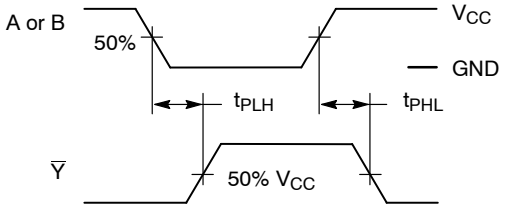
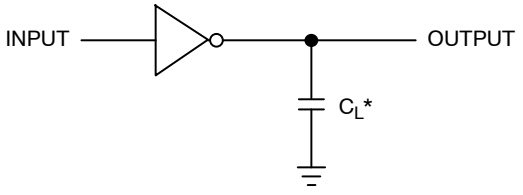


Figure 3. Switching Waveform



*Includes all probe and jig capacitance.
A 1 MHz square input wave is recommended for propagation delay tests.

Figure 4. Test Circuit

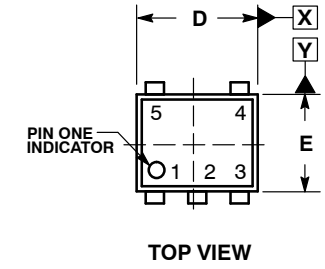
ORDERING INFORMATION

Device	Package	Shipping†
NL17SG14P5T5G	SOT−953 (Pb−Free)	8000 / Tape & Reel

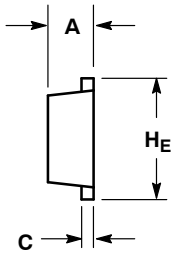
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

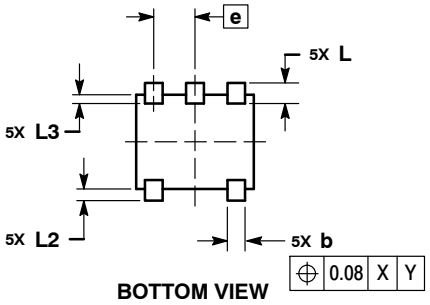
SOT−953
CASE 527AE
ISSUE E



TOP VIEW



SIDE VIEW

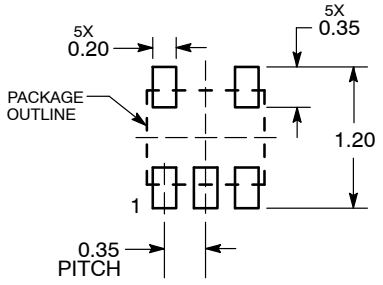


BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H_E	0.95	1.00	1.05
L	0.175 REF		
L2	0.05	0.10	0.15
L3	---	---	0.15

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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